

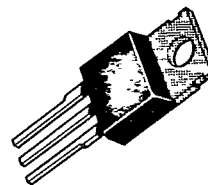
95D 05669 D

T-39-09
ZVN2206**N-channel enhancement
mode vertical DMOS FET****FEATURES**

- Compact geometry
- Fast switching speeds
- No secondary breakdown
- Excellent temperature stability
- High input impedance
- Low current drive
- Ease of paralleling

DESCRIPTION

A compact interdigitated geometry forms the basis of this Ferranti MOSFET. Optimised for low on-resistance, low capacitance and fast switching this device is manufactured using the latest computer controlled processing techniques in order to achieve greater stability, reliability and ruggedness.

TO-39
SUFFIX BTO-220
SUFFIX L**PRODUCT SUMMARY**

Part No.	BV_{DSS}	I_D	$R_{DS(on)}$
ZVN2206B*	60V	4.8A	0.5Ω
ZVN2206L	60V	4.8A	0.5Ω

*BS-CECC approved

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ZVN2206**ABSOLUTE MAXIMUM RATINGS**

Parameters		TO-39	TO-220	Units
V_{DS}	Drain-source voltage	60	60	V
I_D	Continuous drain current (@ $T_A = 25^\circ\text{C}$)	0.9	1.3	A
I_D	Continuous drain current (@ $T_C = 25^\circ\text{C}$)	4.8	4.8	A
I_{DM}	Pulse drain current	16	16	A
V_{GS}	Gate-source voltage	± 20	± 20	V
P_D	Max. power dissipation (@ $T_A = 25^\circ\text{C}$)	0.7	1.5	W
P_D	Max. power dissipation (@ $T_C = 25^\circ\text{C}$)	20	20	W
T_j, T_{stg}	Operating/storage temperature range	-55 to +150		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Min.	Typ.	Max.	Unit	Conditions
BV_{DSS}	Drain-source breakdown voltage	60	-	-	V	$I_D = 10\mu\text{A}, V_{GS} = 0\text{V}$
$V_{GS(th)}$	Gate-source threshold voltage	1	-	3	V	$I_D = 2\text{mA}, V_{DS} = V_{GS}$
I_{GSS}	Gate body leakage	-	-	20	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
I_{DSS}	Zero gate voltage drain current	-	-	2	μA	$V_{DS} = \text{Max. rating}, V_{GS} = 0\text{V}$
		-	-	200	μA	$V_{DS} = 0.8 \times \text{Max. rating}, V_{GS} = 0\text{V} (T = 125^\circ\text{C}) (2)$
$I_{D(on)}$	On-state drain current (1)	4	8	-	A	$V_{DS} = 18\text{V}, V_{GS} = 10\text{V}$
$R_{DS(on)}$	Static drain-source on-state resistance (1)	-	-	0.5	Ω	$I_D = 2\text{A}, V_{GS} = 10\text{V}$
g_{fs}	Forward transconductance (1) (2)	-	1.4	-	S	$V_{DS} = 18\text{V}, I_D = 2\text{A}$
C_{iss}	Input capacitance (2)	-	170	220	pF	} $V_{DS} = 18\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
C_{oss}	Common source output capacitance (2)	-	80	100	pF	
C_{rss}	Reverse transfer capacitance (2)	-	35	80	pF	
$t_{d(on)}$	Turn-on delay time (2) (3)	-	3.7	5	ns	} $V_{DD} \approx 18\text{V}, I_D = 2\text{A}$
t_r	Rise time (2) (3)	-	14	20	ns	
$t_{d(off)}$	Turn-off delay time (2) (3)	-	17	26	ns	
t_f	Fall time (2) (3)	-	18	25	ns	

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SOURCE-DRAIN DIODE CHARACTERISTICS

Parameter	Typ.	Unit	Conditions
V_{SD}	0.95	V	$V_{GS} = 0V, I_S = 4A$
t_{rr}	59	ns	$V_{GS} = 0V, I_F = 4A, I_R = 1A$

- (1) Measured under pulsed conditions. Width = 300 μ s. Duty cycle \leq 2%.
- (2) Sample test.
- (3) Switching times measured with 50 Ω source impedance and < 5ns rise time on a pulse generator.

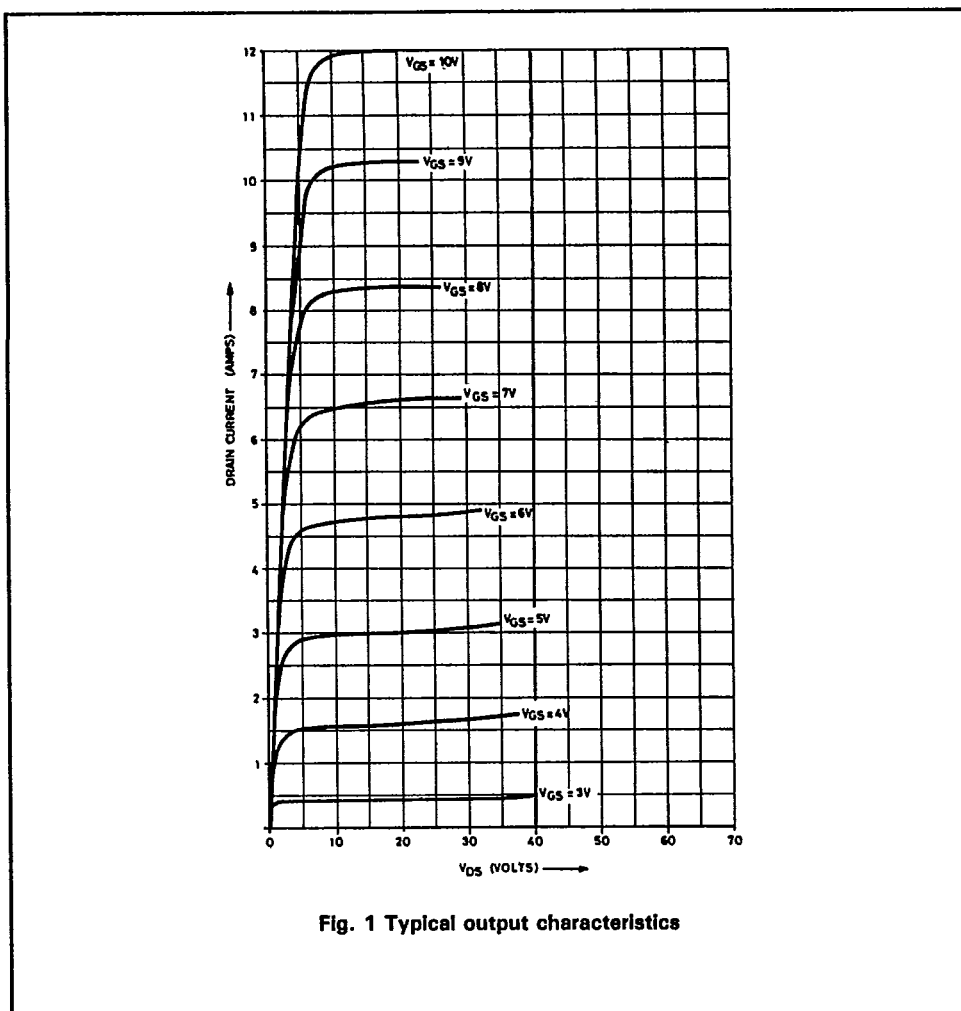


Fig. 1 Typical output characteristics

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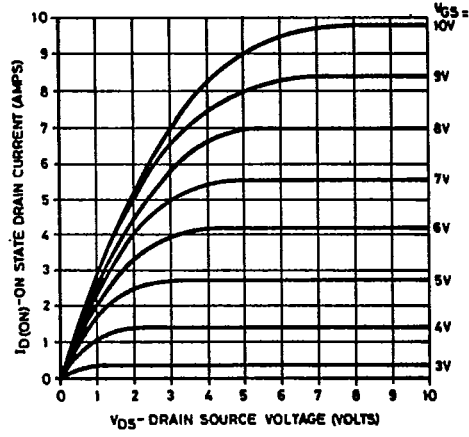


Fig. 2 Typical saturation characteristics

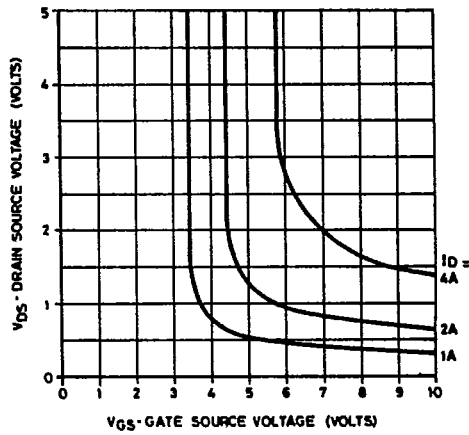


Fig. 3 Typical voltage saturation characteristics

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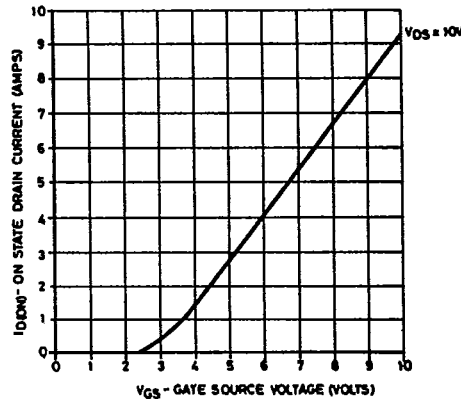


Fig. 4 Typical transfer characteristics

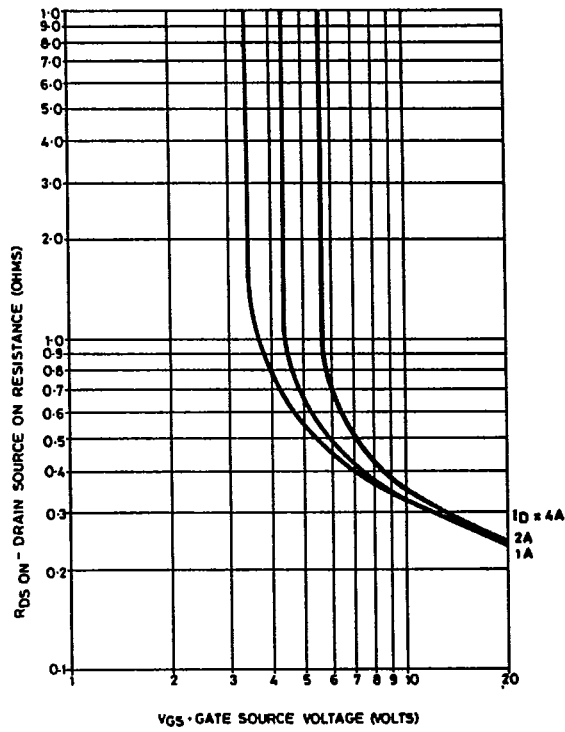


Fig. 5 Typical on-resistance v gate-source voltage

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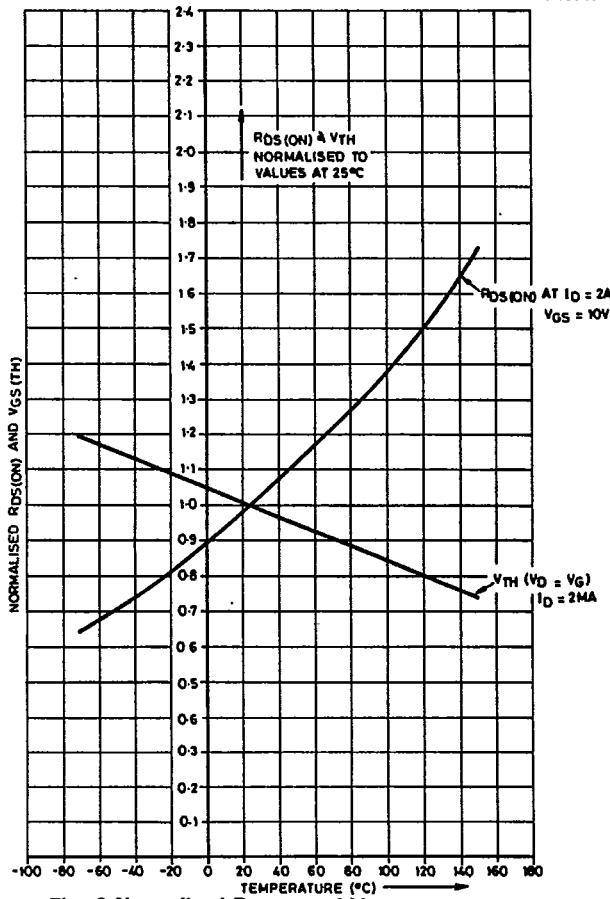


Fig. 6 Normalised $R_{DS(on)}$ and $V_{GS(th)}$ v temperature

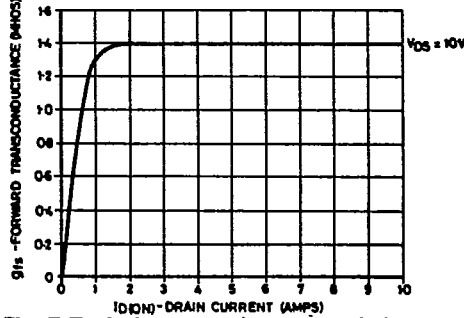


Fig. 7 Typical transconductance v drain current

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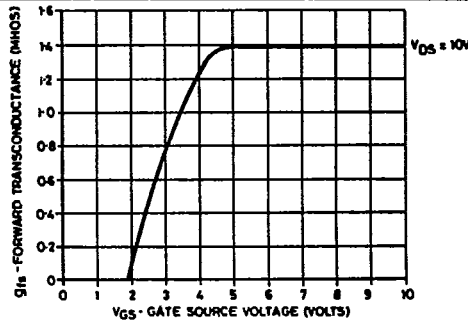


Fig. 8 Typical transconductance v gate-source voltage

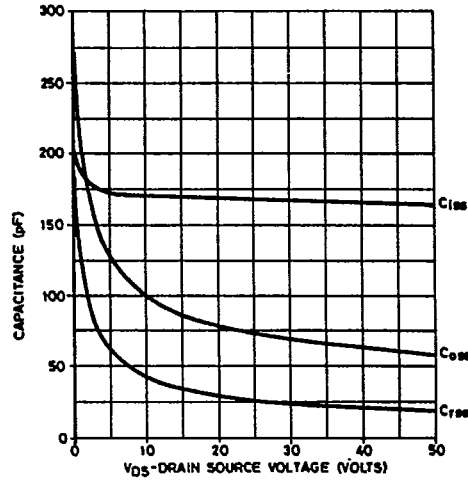


Fig. 9 Typical capacitance v drain-source voltage

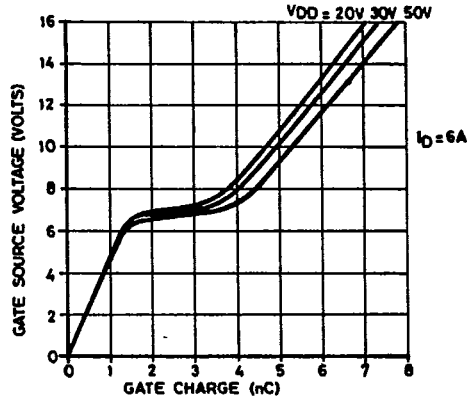


Fig. 10 Typical gate charge v gate-source voltage

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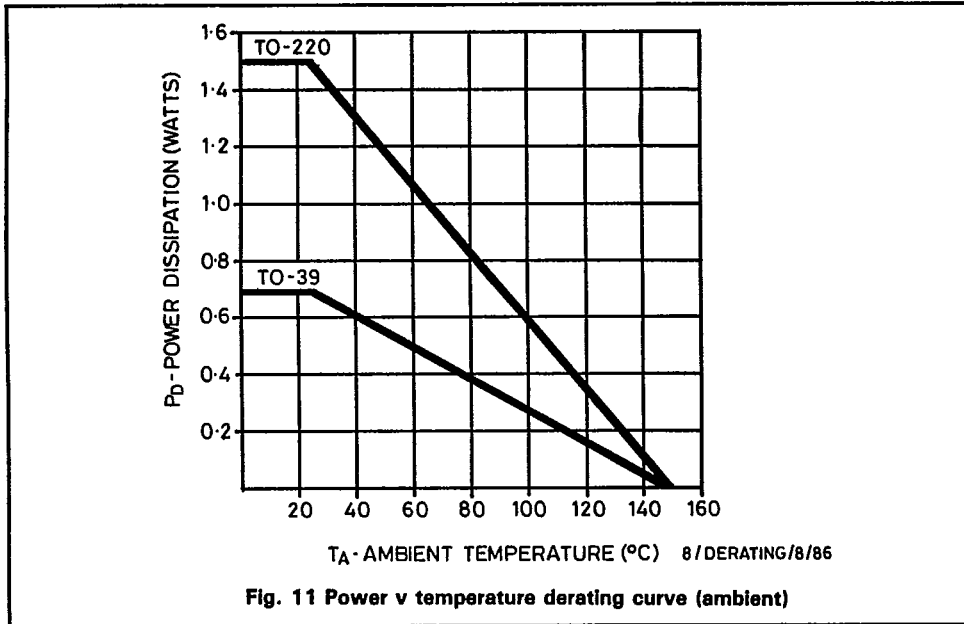


Fig. 11 Power v temperature derating curve (ambient)

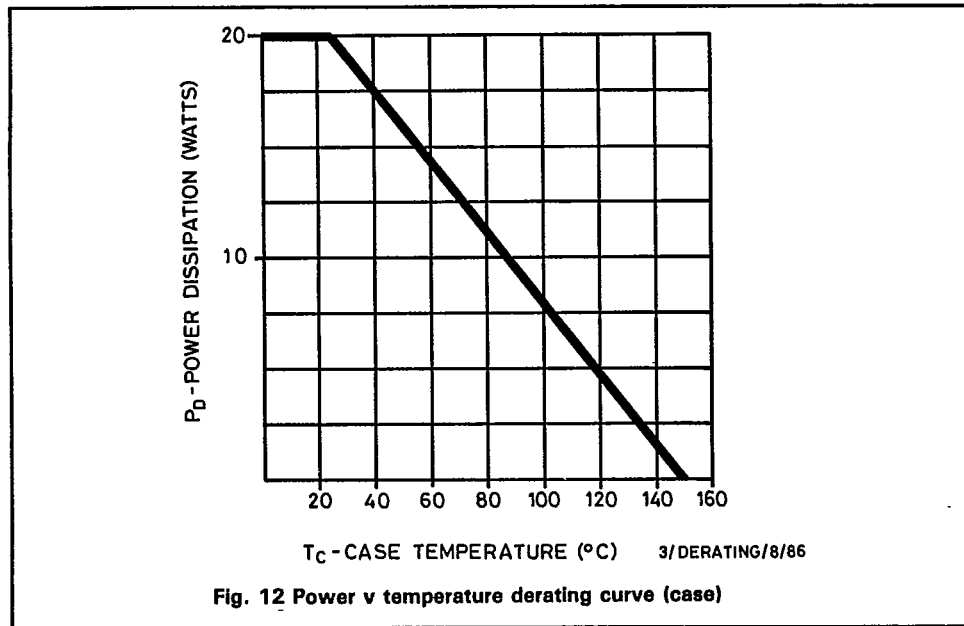


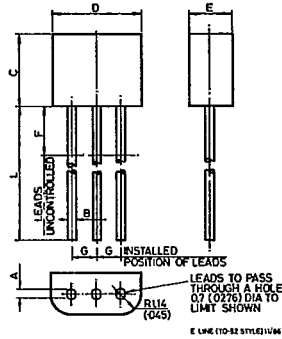
Fig. 12 Power v temperature derating curve (case)

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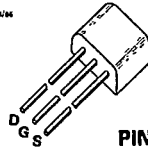
PACKAGE DETAILS

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E-Line (TO-92 style)



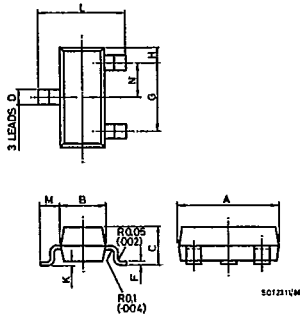
DIMENSION	MILLIMETRES		INCHES	
	MIN	MAX	MIN	MAX
A	0.41	0.495	0.016	0.0195
B	0.41	0.495	0.016	0.0195
C	3.61	4.01	0.142	0.158
D	4.37	4.77	0.172	0.188
E	2.16	2.41	0.085	0.095
F		2.5		0.098
G	1.27 NOM		0.050 NOM	
L	12.06	13.97	0.475	0.550



PIN CONFIGURATION

Available on tape on reels. Please enquire for details.

SOT-23



DIMENSION	MILLIMETRES		INCHES	
	MIN	MAX	MIN	MAX
A	2.75	3.04	0.108	0.120
B	1.2	1.4	0.047	0.055
C	0.89	1.12	0.035	0.044
D	0.37	0.43	0.0145	0.017
F	0.085	0.14	0.0034	0.0055
G	1.78	2.04	0.070	0.080
H	0.33	0.51	0.013	0.020
K	0.075	0.125	0.003	0.005
L	2.10	2.5	0.0825	0.0985
M	0.45	0.64	0.018	0.025
N	0.89	1.02	0.035	0.040



PIN CONFIGURATION

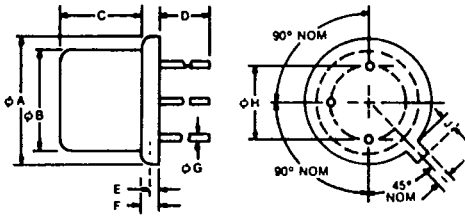
Available in tape on reels. Please enquire for details.

95D 05844 D

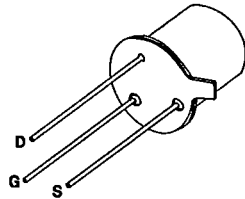
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PACKAGE DETAILS

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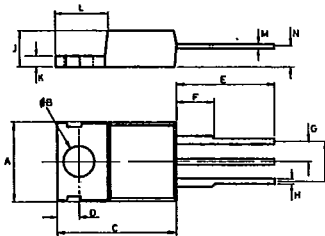


DIMENSION	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
∅A	0.350	0.370	8.99	9.40
∅B	0.306	0.335	7.77	8.51
C	0.240	0.260	6.10	6.60
D	0.500		12.70	
E	0.009	0.023	0.229	0.548
F	0.018	0.045	0.458	1.143
∅G	0.016	0.021	0.406	0.533
∅H	0.190	0.210	4.83	5.33
I	0.028	0.037	0.711	0.939
J	0.026	0.040	0.660	1.016

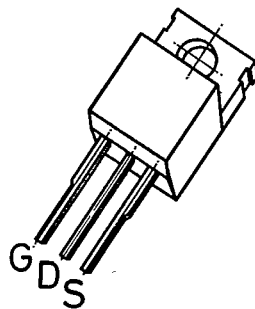


PIN CONFIGURATION

TO-220



DIMENSION	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
A	0.387	0.403	9.8	10.2
∅B	0.139	0.147	3.53	3.73
C	0.612	0.648	15.56	16.46
D	0.10	0.12	2.55	3.05
E	0.50	0.56	12.71	14.21
F		0.25		6.35
G	0.09	0.11	2.29	2.79
H	0.022	0.032	0.57	0.83
I	0.19	0.21	4.85	5.35
J	0.17	0.19	4.32	4.82
K	0.045	0.055	1.14	1.4
L	0.245	0.265	6.23	6.73
M	0.015	0.025	0.37	0.63
N	0.085	0.105	2.15	2.65



PIN CONFIGURATION